## EAST Search History

| Ref# | Hits  | Search Query   | DBs  | Default<br>Operator | Plurals | Time Stamp          |
|------|-------|--|--|---------------------|---------|---------------------|
| 51   | 62    | (US-20070030623-\$ or US-20060098362-\$ or US-20060286737-\$ or US-20030178620-\$ or US-20040184216-\$ or US-20040184216-\$ or US-20030183866-\$).did. or (US-7064345-\$ or US-5705826-\$ or US-5705826-\$ or US-6087196-\$ or US-6087196-\$ or US-7193237-\$ or US-7193237-\$ or US-7198977-\$ or US-6556791-\$ or US-6331356-\$ or US-631356-\$ or US-6219170-\$ or US-6555840-\$ or US-6555840-\$ or US-699299-\$ or US-699296-\$ or US-699296-\$ or US-699296-\$ or US-65506525-\$ or US-6990296-\$ or US-6990296-\$ or US-6950299-\$ or US-6703681-\$).did. or (US-3512052-\$ or US-3508123-\$).did. or (DE-10219905-\$).did. or (JP-2001085272-\$).did. or (JP-2001085272-\$).did. | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ                 | ON      | 2009/02/12          |
| S2   | 5     | (metal or conductive or<br>electrode) and<br>semiconductor near3<br>layer and voltage with<br>capcitance   | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ                 | ON      | 2009/02/12<br>14:00 |
| S3   | 12170 | (metal or conductive or<br>electrode) and<br>semiconductor near3<br>layer and voltage with<br>capacitance  | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ                 | ON      | 2009/02/12<br>14:01 |

| S4         | 7427 | (metal or conductive or electrode) and semiconductor near3 layer and voltage with capacitance and (varactor or capacitor or condensor)   | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON    | 2009/02/12<br>14:01 |
|------------|------|--|--|-----|-------|---------------------|
| S5         | 2171 | (metal or conductive or electrode) and semiconductor near3 layer and voltage with capacitance and (varactor or capacitor or condensor).ab,ti.  | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON    | 2009/02/12<br>14:01 |
| S6         | 2170 | (metal or conductive or electrode) and semiconductor near3 layer and voltage with capacitance and (varactor or capacitor or condensor).ab,ti. not eletrolytic  | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ |       | 2009/02/12<br>14:02 |
| <b>S</b> 7 | 116  | (metal or conductive or electrode) and semiconductor near3 layer and voltage with (varied or varing or variable or vary) capacitance and (varactor or capacitor or condensor).ab,ti. not eletrolytic             | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ···ON | 2009/02/12<br>14:02 |
| S8         | 2043 | (metal or conductive or electrode) and semiconductor near3 layer and voltage with capacitance and (varactor or capacitor or condensor).ab,ti. not electrolytic   | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON    | 2009/02/12<br>14:12 |
| <b>S</b> 9 | 94   | (metal or conductive or electrode) and semiconductor near3 layer and voltage with (variable or tunable or controlable or trimmable) capacitance and (varactor or capacitor or condensor).ab,ti. not electrolytic | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ |       | 2009/02/12<br>14:20 |

| S10 | 192  | (metal or conductive or electrode) and semiconductor near3 layer and voltage with (variable or tunable or controlable or trimmable) with capacitance and (varactor or capacitor or condensor).ab,ti. not electrolytic | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>14:21 |
|-----|------|---|--|-----|-----|---------------------|
| S11 | 380  | (metal or conductive or electrode) and semiconductor near3 layer and voltage with (varied or varing or variable or vary) with capacitance and (varactor or capacitor or condensor).ab,ti. not eletrolytic             | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>14:21 |
| S12 | 6408 | metal semiconductor<br>metal or MSM   | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>14:42 |
| S13 | 1410 | metal semiconductor<br>metal or MSM and<br>(varactor or capcitor or<br>condensor)   | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>14:42 |
| S14 | 1696 | metal semiconductor<br>metal or MSM and<br>(varactor or capacitor or<br>condensor)  | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>14:42 |
| S15 | 566  | (metal semiconductor<br>metal or MSM) and<br>(varactor or capacitor or<br>condensor)  | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>14:44 |
| S16 | 1    | ("6414369").PN.   | US-PGPUB;<br>USPAT; USOCR                          | OR  | OFF | 2009/02/12<br>14:46 |
| S18 | 2    | ("5614727"   "5719647").<br>PN. OR ("6414369").<br>URPN.  | US-PGPUB;<br>USPAT; USOCR                          | ADJ | ON  | 2009/02/12<br>15:00 |
| S19 | 9419 | pn junction and (varactor or capacitor or condensor)  | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>15:03 |
| S20 | 2047 | pn junction and (varactor or capacitor or condensor).ab,ti.   | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>15:03 |

| S21 | 91   | pn junction and (varactor<br>or capacitor or<br>condensor).ab,ti. and<br>"361".clas.  | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>15:04 |
|-----|------|---|--|-----|-----|---------------------|
| S22 | 50   | (metal semiconductor<br>metal or MSM) and<br>(varactor or capacitor or<br>condensor).ab,ti.                                 | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>15:07 |
| S23 | 145  | pn and (varactor or capacitor or condensor).<br>ab,ti. and "361".clas.  | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>15:11 |
| S24 | 48   | pn same semiconductor<br>and (varactor or<br>capacitor or condensor).<br>ab,ti. and "361".clas.                             | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/12<br>15:11 |
| S25 | 1    | ("20040184216").PN.   | US-PGPUB;<br>USPAT; USOCR                          | OR  | OFF | 2009/02/17<br>08:12 |
| S26 | 4795 | semiconduct\$4 with<br>(insulat\$4 or dielectric)<br>with frequency   | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/17<br>08:28 |
| S27 | 1588 | semiconduct\$4 with (insulat\$4 or dielectric) with frequency and (capacitor or condensor or varactor)                      | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/17<br>08:28 |
| S28 | 1148 | semiconduct\$4 with (insulat\$4 or dielectric) with frequency and (capacitor or condensor or varactor) and voltage          | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/17<br>08:28 |
| S29 | 728  | semiconduct\$4 with (insulat\$4 or dielectric) with frequency and (capacitor or condensor or varactor).ab,ti,clm.           | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/17<br>08:29 |
| S30 | 67   | semiconduct\$4 with (insulat\$4 or dielectric) with frequency and (varactor).ab,ti,clm.                                     | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/17<br>08:31 |
| S31 | 8    | semiconduct\$4 with (insulat\$4 or dielectric) with frequency with act and (varactor or capacitor or condensor). ab,ti,clm. | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/17<br>09:04 |
| S32 | 46   | semiconduct\$4 with<br>(insulat\$4 or dielectric)<br>with frequency with act  | US-PGPUB;<br>USPAT;<br>USOCR; EPO;<br>JPO; DERWENT | ADJ | ON  | 2009/02/17<br>09:07 |

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